

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT54 plastic package. This sensitive gate "series E" triac is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

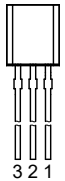
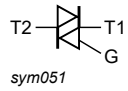
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|------|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{lead} \leq 51\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 1 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 12.5 | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | - | 13.7 | A |
| T_j | junction temperature | | - | - | 125 | °C |
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7 | - | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7 | - | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7 | - | - | 10 | mA |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------|
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; Fig. 7 | - | - | 10 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9 | - | 1.3 | 10 | mA |
| V_T | on-state voltage | $I_T = 1.4\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.2 | 1.5 | V |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$ | 50 | - | - | V/ μ s |
| dV_{com}/dt | rate of change of commutating voltage | $V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $dI_{com}/dt = 0.5\text{ A/ms}$; $I_T = 1\text{ A}$; gate open circuit | 5 | - | - | V/ μ s |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------|---|--|
| 1 | T2 | main terminal 2 |  <p>TO-92 (SOT54)</p> |  <p>sym051</p> |
| 2 | G | gate | | |
| 3 | T1 | main terminal 1 | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BT131-800E | TO-92 | plastic single-ended leaded (through hole) package; 3 leads | SOT54 |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|---|-----|------|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{lead} \leq 51\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 1 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | 12.5 | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | 13.7 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; SIN | - | 0.78 | A ² s |
| di_T/dt | rate of rise of on-state current | $I_G = 20\text{ mA}$ | - | 50 | A/ μ s |
| | | | - | 50 | A/ μ s |
| | | | - | 10 | A/ μ s |
| | | | - | 50 | A/ μ s |
| I_{GM} | peak gate current | | - | 2 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.1 | W |
| T_{stg} | storage temperature | | -40 | 150 | °C |
| T_j | junction temperature | | - | 125 | °C |



Fig. 1. RMS on-state current as a function of lead temperature; maximum values

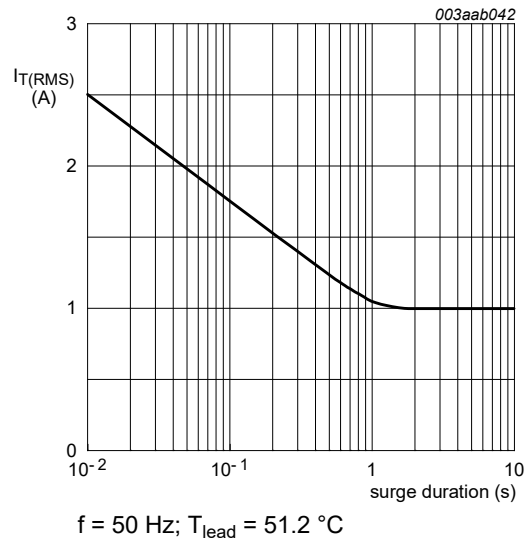


Fig. 2. RMS on-state current as a function of surge duration; maximum values

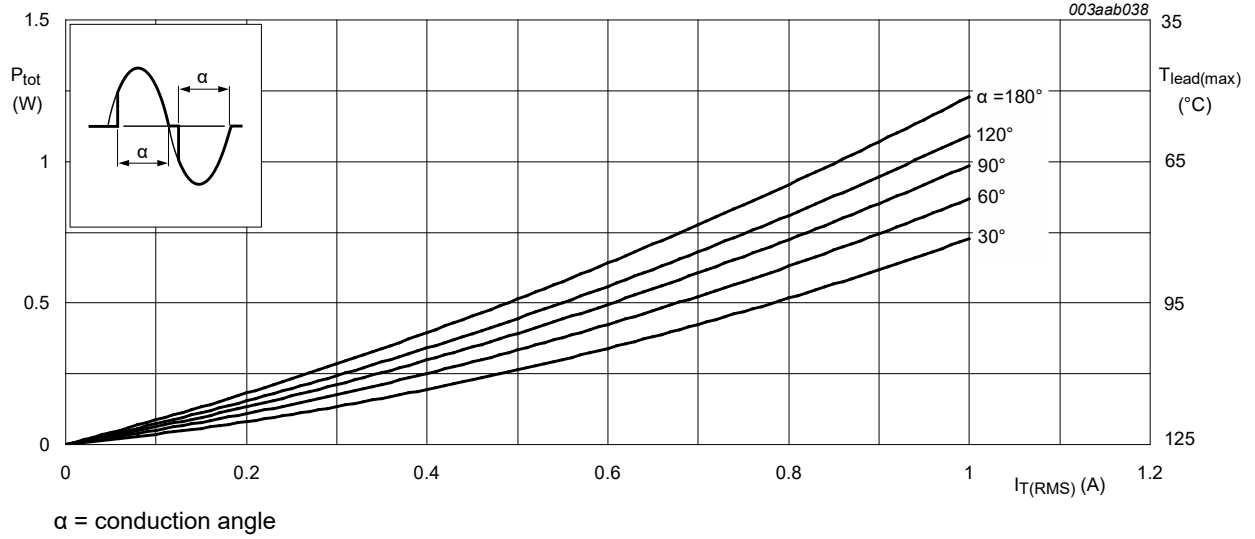


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

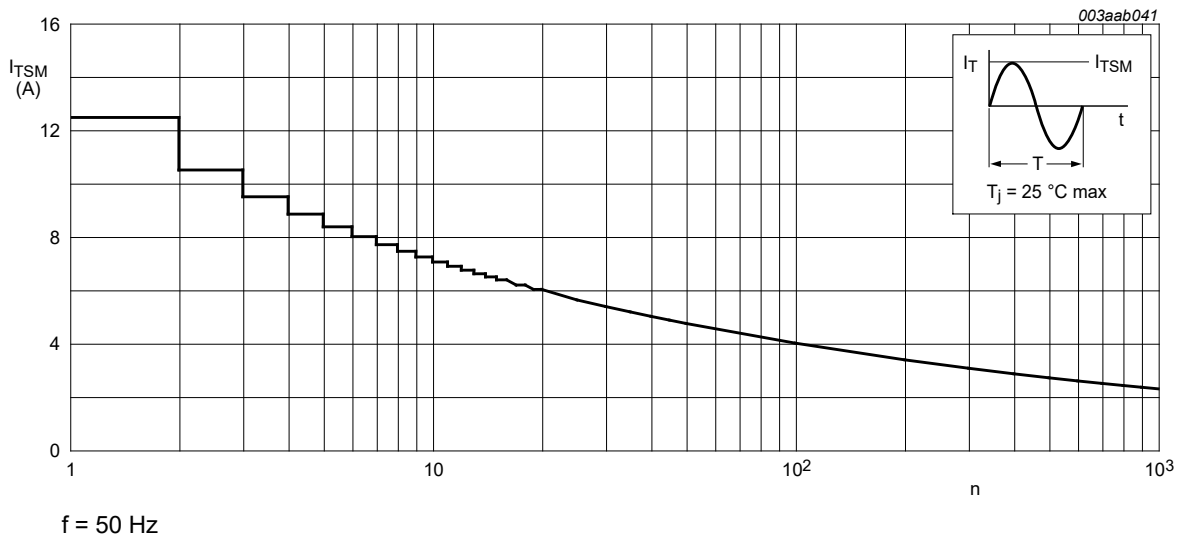


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------|--|---|-----|-----|-----|------|
| R _{th(j-lead)} | thermal resistance from junction to lead | full cycle; Fig. 6 | - | - | 60 | K/W |
| | | half cycle; Fig. 6 | - | - | 80 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | printed circuit board mounted: lead length = 4 mm | - | 150 | - | K/W |



9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|-----|-----|-----|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | - | - | 10 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | - | - | 10 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | - | - | 10 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7 | - | - | 10 | mA |
| I_L | latching current | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 15 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 15 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 25 | mA |
| | | $V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8 | - | - | 15 | mA |
| I_H | holding current | $V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9 | - | 1.3 | 10 | mA |
| V_T | on-state voltage | $I_T = 1.4\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10 | - | 1.2 | 1.5 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11 | - | 0.7 | 1 | V |
| | | $V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C};$ Fig. 11 | 0.2 | 0.3 | - | V |
| I_D | off-state current | $V_D = 800\text{ V}; T_j = 125\text{ }^\circ\text{C}$ | - | 0.1 | 0.5 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$ | 50 | - | - | V/ μ s |
| dV_{com}/dt | rate of change of commutating voltage | $V_D = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}; dI_{com}/dt = 0.5\text{ A/ms}; I_T = 1\text{ A};$ gate open circuit | 5 | - | - | V/ μ s |
| t_{gt} | gate-controlled turn-on time | $I_{TM} = 1.5\text{ A}; V_D = 800\text{ V}; I_G = 0.1\text{ A}; dI_G/dt = 5\text{ A}/\mu\text{s}$ | - | 2 | - | μ s |

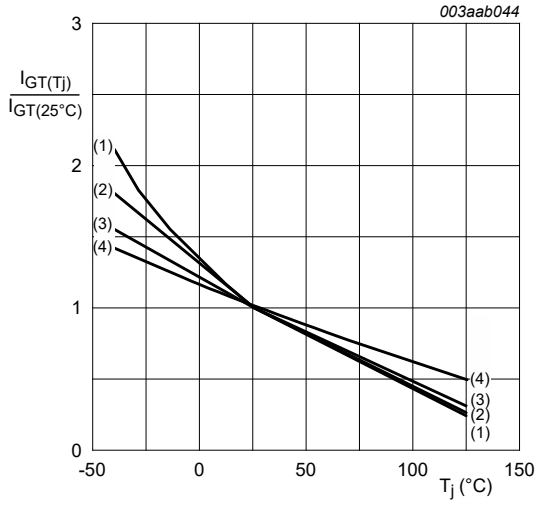


Fig. 7. Normalized gate trigger current as a function of junction temperature



Fig. 8. Normalized latching current as a function of junction temperature

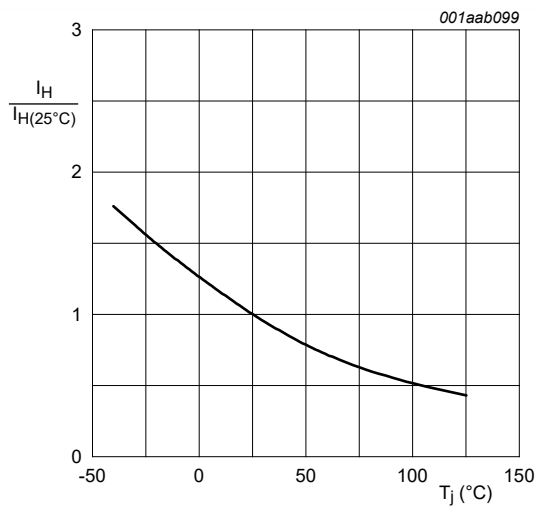


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.92\text{ V}; R_s = 0.4\ \Omega$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

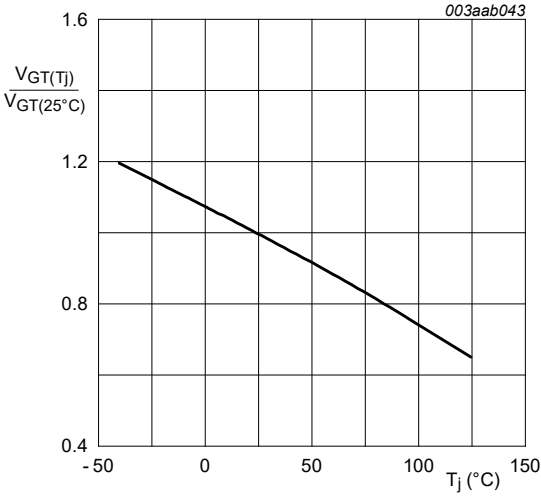


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

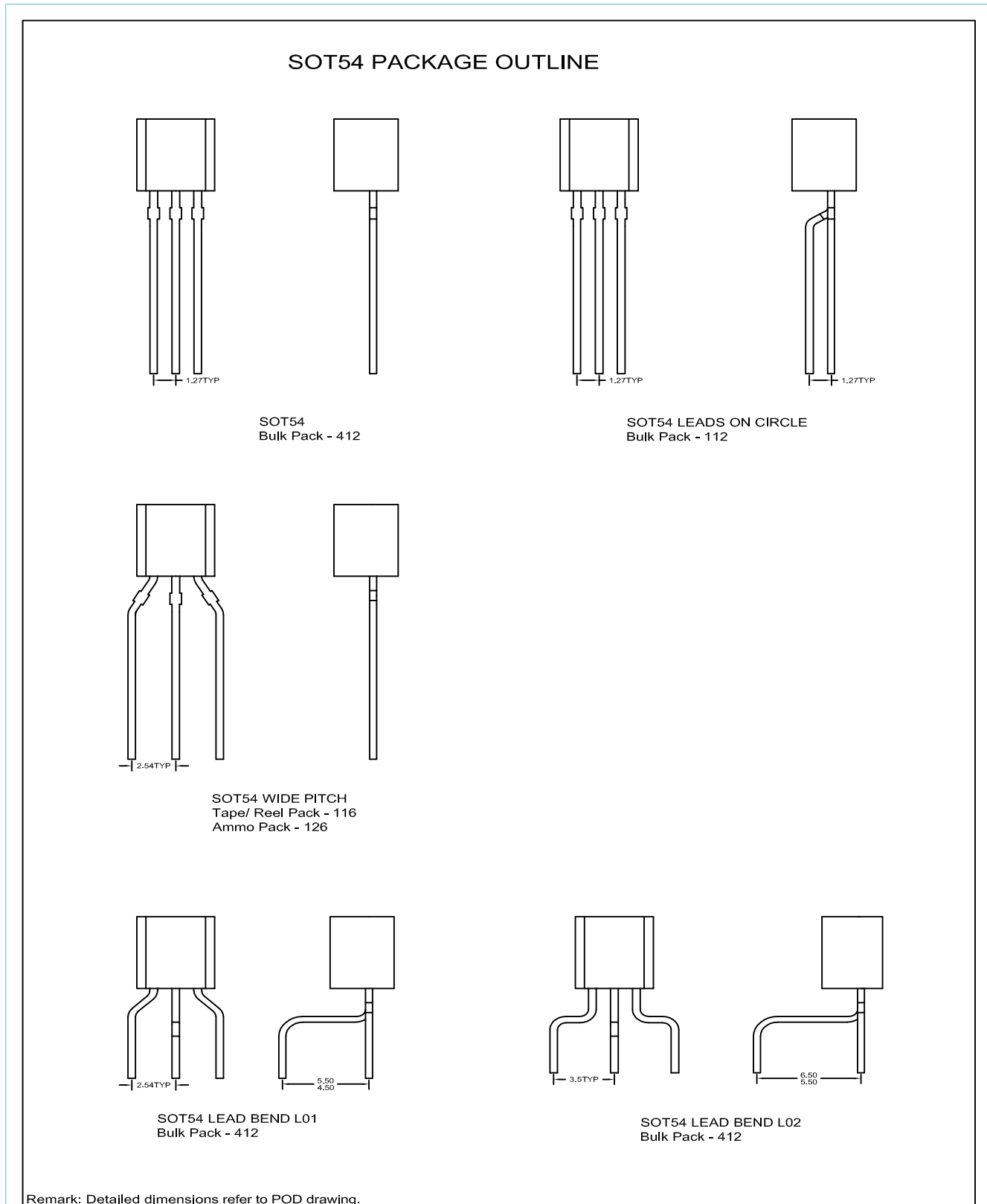


Fig. 12. Package outline TO-92 (SOT54)

11. Legal information

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|--------------------------------|--------------------|---|
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- [2] The term 'short data sheet' is explained in section "Definitions".
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